

LISTINGS OF THE CLAIMS

This listing of the claims will replace all prior versions, and listings of claims in the application.

Listing of the Claims:

This listing of claims will replace all previous versions of the claims:

1. (Previously Presented) A transreflective liquid crystal display device, comprising:
 - a first substrate including a transmissive pixel and a reflective pixel;
 - a plurality of gate lines and a plurality of data lines on the first substrate, the gate and data lines crossing each other to define a pixel region, the transmissive and reflective pixels correspond to respective pixel regions;
 - a thin film transistor at each crossing of the gate and data lines;
 - a first passivation layer covering the thin film transistor, the first passivation layer having a transmissive hole in the transmissive pixel;
 - a first reflector on the first passivation layer in the reflective pixel;
 - a second passivation layer in the transmissive pixel;
 - a pixel electrode on the second passivation layer;
 - a second substrate spaced apart from and facing the first substrate;
 - a color filter layer on an inner surface of the second substrate, the color filter layer containing red (R), green (G) and blue (B) sub color filters, each sub color filter corresponding to one of the pixel regions;
 - a liquid crystal layer between the first and second substrates; and
 - a second reflector between the first and second passivation layers in the transmissive pixel, the second reflector covering sides of the first passivation layer corresponding to the transmissive hole,wherein the second reflector overlaps the data lines.

2 – 3. (Cancelled)

4. (Original) The device according to claim 1, wherein the thin film transistor has a bottom gate structure, which includes a gate electrode, a gate insulating layer on the gate electrode, an active layer of amorphous silicon on the

gate insulating layer, an ohmic contact layer of doped amorphous silicon on the active layer, source and drain electrodes on the ohmic contact layer.

5. (Previously Presented) The device according to claim 1, wherein the thin film transistor has a top gate structure, which includes a semiconductor layer of polycrystalline silicon having an active area and source and drain areas, a gate insulating layer on the semiconductor layer, a gate electrode on the gate insulating layer over the active area, an inter insulating layer on the gate electrode, and source and drain electrodes on the inter insulating layer, the source and drain electrodes are connected to the source and drain areas, respectively.

6. (Original) The device according to claim 1, wherein three pixel regions of R, G and B extending in a first direction parallel with the gate lines constitute one dot.

7. (Original) The device according to claim 6, wherein the transmissive pixel and the reflective pixel are alternately arranged in the first direction.

8. (Original) The device according to claim 7, wherein the dot includes one transmissive pixel and two reflective pixels.

9. (Original) The device according to claim 7, wherein the dot includes two transmissive pixels and one reflective pixel.

10. (Previously Presented) The device according to claim 6, wherein the dots include a transmissive dot having three transmissive pixels and a reflective dot having three reflective pixels.

11. (Previously Presented) The device according to claim 10, wherein the transmissive and reflective dots are alternately arranged in the first direction.

12. (Previously Presented) The device according to claim 11, wherein the transmissive and reflective dots are alternately arranged in a second direction orthogonal to the first direction.

13. (Previously Presented) The device according to claim 7, wherein the transmissive and reflective pixels are alternately arranged in a second direction orthogonal to the first direction.

14. (Original) The device according to claim 1, wherein the second passivation layer is disposed on the first reflector.

15. (Previously Presented) The device according to claim 1, wherein the first passivation layer has an uneven surface and the first reflector formed on the uneven surface of the first passivation layer is uneven.

16. (Original) The device according to claim 15, wherein the first passivation layer has an even surface between the first reflector and the second reflector and on which the first reflector is not formed.

17. (Original) The device according to claim 16, wherein the even surface of the first passivation layer essentially corresponds to an area above which the data lines are formed.

18. (Original) The device according to claim 17, wherein the second passivation layer covers at least a portion of the even surface.

19. (Original) The device according to claim 15, wherein the second passivation layer separates the second reflector from the first reflector.

20. (Original) The device according to claim 15, wherein no portion of the first passivation over which the second reflector is formed has an uneven surface

21. (Original) The device according to claim 1, wherein the transmissive hole is formed in an area adjacent to the transistor in a direction parallel with the gate lines.

22. (Original) The device according to claim 1, wherein the pixel electrode is formed in the reflective pixel.

23. (Original) The device according to claim 22, wherein the pixel electrode is connected to the thin film transistor.

24. (Currently Amended) A transflective liquid crystal display device, comprising:
- a first substrate including a transmissive pixel and a reflective pixel;
 - a plurality of gate lines and a plurality of data lines on the first substrate, the gate and data lines crossing each other to define a pixel region, the transmissive pixel and the reflective pixel corresponding to respective pixel regions;
 - a thin film transistor at each crossing of the gate and data lines;
 - a first passivation layer covering the thin film transistor, the first passivation layer having a transmissive hole in the transmissive pixel;
 - a reflective electrode on the first passivation layer in the reflective pixel, the reflective electrode connected to the thin film transistor;
 - a pixel electrode disposed in the transmissive pixel and connected to the thin film transistor;
 - a second substrate spaced apart from and facing the first substrate;
 - a color filter layer on an inner surface of the second substrate, the color filter layer containing red (R), green (G) and blue (B) sub color filters, each sub color filter corresponding to one of the pixel regions; and
 - a liquid crystal layer between the first and second substrates;
 - a second passivation layer disposed in the transmissive pixel on which the pixel electrode is disposed; and
 - a reflector between the first and second passivation layers in the transmissive pixel,
wherein the reflector covers sides of the first passivation layer
corresponding to the transmissive hole, and wherein the reflector overlaps the data lines.

25 - 26. (Cancelled)

27. (Previously Presented) The device according to claim 25, wherein the second passivation layer does not cover the reflective electrode.

28. (Previously Presented) The device according to claim 27, wherein the second passivation layer terminates before extending into the reflective pixel.

29. (Previously Presented) The device according to claim 25, wherein the first passivation layer has an uneven surface and the reflective electrode formed on the uneven surface of the first passivation layer is uneven.

30. (Previously Presented) The device according to claim 29, wherein the first passivation layer has an even surface between the reflective electrode and the reflector on which the reflective electrode is not formed.

31. (Previously Presented) The device according to claim 30, wherein the even surface of the first passivation layer essentially corresponds to an area above which the data lines are formed.

32. (Previously Presented) The device according to claim 31, wherein the second passivation layer covers at least a portion of the even surface.

33. (Previously Presented) The device according to claim 31, wherein the pixel electrode terminates before extending substantially into an area over the portion of the even surface.

34. (Previously Presented) The device according to claim 25, wherein the second passivation layer covers the reflector and separates the reflector from the reflective electrode.

35. (Previously Presented) The device according to claim 25, wherein no portion of the first passivation over which the reflector is formed has an uneven surface.

36. (Previously Presented) The device according to claim 24, wherein the thin film transistor has a bottom gate structure, which includes a gate electrode, a gate insulating layer on the gate electrode, an active layer of amorphous silicon on the gate insulating layer, an ohmic contact layer of doped amorphous silicon on the active layer, source and drain electrodes on the ohmic contact layer.

37. (Previously Presented) The device according to claim 24, wherein the thin film transistor has a top gate structure, which includes a semiconductor layer of polycrystalline silicon having an active area and source and drain areas, a gate insulating layer on the semiconductor layer, a gate electrode on the gate insulating

layer over the active area, an inter insulating layer on the gate electrode, and source and drain electrodes on the inter insulating layer, the source and drain electrodes are connected to the source and drain areas, respectively.

38. (Previously Presented) The device according to claim 24, wherein three pixel regions of R, G and B extending in a first direction parallel with the gate lines constitute one dot.

39. (Previously Presented) The device according to claim 38, wherein the transmissive pixel and the reflective pixel are alternately arranged in the first direction.

40. (Previously Presented) The device according to claim 39, wherein the dot includes one transmissive pixel and two reflective pixels.

41. (Previously Presented) The device according to claim 39, wherein the dot includes two transmissive pixels and one reflective pixel.

42. (Previously Presented) The device according to claim 38, wherein the dots include a transmissive dot having three transmissive pixels and a reflective dot having three reflective pixels.

43. (Previously Presented) The device according to claim 42, wherein the transmissive dot and the reflective dot are alternately arranged in the first direction.

44. (Previously Presented) The device according to claim 43, wherein the transmissive and reflective dots are alternately arranged in a second direction orthogonal to the first direction.

45. (Previously Presented) The device according to claim 24, wherein the transmissive hole is formed in an area adjacent to the transistor in a direction parallel with the gate lines.

46 – 53. (Cancelled)